

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	28779	Micron.As.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:48
2	L2	1592	1 and radiation	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:48
3	L3	6	2 and photo-definable	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:50

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4	L4	7	2 and "positive mask"	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:53
5	L5	67414	Howard.in.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:53
6	L6	3000	5 and radiation	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:53

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7	L7	8	6 and "positive mask"	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:53
8	L8	5	("4921321" "4978594" "5215861" "5439780" "5885751").PN.	US- PGPUB; USPAT; USOCR	2005/06/22 13:54
9	L9	8	("5885751").URPN.	USPAT	2005/06/22 13:56
10	L10	8	("5885751").URPN.	USPAT	2005/06/22 13:56
11	L11	4	("6350706").URPN.	USPAT	2005/06/22 13:56
12	L12	36	((plasma adj polymer\$6 adj methylsilane) or PPMS) and (DRAM or SRAM or SDRAM or FLASH)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:57
13	L13	533	((positiv\$6 near8 (mask\$6 or resist\$4 or PR or photoresist\$3 or photo- resist\$3 or (organo adj silicon) or organosilicon or photodefinable or photo- definable)) same (DUV or UV or radiat\$6 or light\$6 or electromag\$6)) same (trench\$4 or interconnect\$6 or damascene)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:57

	L #	Hits	Search Text	DBs	Time Stamp
14	L14	14	1 and 13	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2005/06/22 13:58

US-PAT-NO: 6274897

DOCUMENT-IDENTIFIER: US 6274897 B1

TITLE: Semiconductor structure having interconnects
on a
projecting region and substrate

----- KWIC -----

Assignee Name - ASNM (1):
Micron Technology, Inc.

Detailed Description Text - DETX (8):

In addition to reducing the aspect ratios of trenches 20 (FIG. 1), which are formed when the word lines 12 are etched from the layer 30, such planarizing of the layer 30 reduces or eliminates inaccuracies in the photoresist etch mask (not shown) for the layer 30. Often, the depressions between the peaks of the unlevel layer 30 form parabolic bowls. During the photolithography for forming the etch mask for the layer 30, these bowls may focus light in such a way as to cause an erroneous exposure (or nonexposure, depending upon whether positive or negative photoresist is used) of the photoresist. Such erroneous exposure may cause unwanted mask openings (or unwanted mask formation in the case of negative photoresist) that allow etching (or nonetching) of portions of the layer 30 that should not (should) be etched.

US-PAT-NO: 5851734

DOCUMENT-IDENTIFIER: US 5851734 A
See image for Certificate of Correction

TITLE: Process for defining resist patterns

----- KWIC -----

Assignee Name - ASNM (1):

Micron Technology, Inc.

Brief Summary Text - BSTX (8):

In FIG. 1a, the mask 14, which may be formed of a quartz material 16, contains a chrome material 18 which has been deposited thereon and which specifies the pattern to be defined in the resist. When ultraviolet light from source 17 is passed through the mask, the resist material underlying the chrome 18 is not exposed to the ultraviolet light, while the resist material underlying areas of the mask where there is no chrome is exposed to ultraviolet light. If positive resist material is used, only resist line 12' of width W remains after development and rinsing as shown in FIG. 1b. If negative resist is used, a trench 19 of width W is formed in the resist material after development and rinsing as shown in FIG. 1c. Thus, the width of chrome area 18 of the mask 14 defines the width W of a pattern to be formed in resist 12.